

## Automotive N-Channel 40 V (D-S) 175 °C MOSFET

PRODUCT SUMMARY				
V <sub>DS</sub> (V)	40			
$R_{DS(on)}$ ( $\Omega$ ) at $V_{GS}$ = 10 V	0.0012			
$R_{DS(on)}$ ( $\Omega$ ) at $V_{GS} = 4.5 \text{ V}$	0.0015			
I <sub>D</sub> (A)	160			
Configuration	Single			
Package	PowerPAK 8x8L			

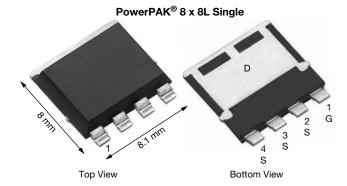
#### **FEATURES**

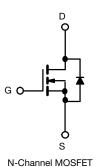
- TrenchFET® power MOSFET
- AEC-Q101 qualified
- 100 % R<sub>q</sub> and UIS tested
- Fully lead (Pb)-free device
- Thin 1.9 mm height
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>











<b>ABSOLUTE MAXIMUM RATING</b>	S (T <sub>C</sub> = 25 °C, unless	otherwise noted	)	
PARAMETER	SYMBOL	LIMIT	UNIT	
Drain-Source Voltage		V <sub>DS</sub>	40	V
Gate-Source Voltage		V <sub>GS</sub>	± 20	V
Continuous Drain Current	T <sub>C</sub> = 25 °C <sup>a</sup>	1	160	
Continuous Drain Current	T <sub>C</sub> = 125 °C	I <sub>D</sub>	146	
Continuous Source Current (Diode Conduc	tion)	I <sub>S</sub>	124	Α
Pulsed Drain Current b		I <sub>DM</sub>	200	
Single Pulse Avalanche Current		I <sub>AS</sub>	50	
Single Pulse Avalanche Energy	le Pulse Avalanche Energy		125	mJ
Maximum Dayyar Discipation	T <sub>C</sub> = 25 °C	Б	136	W
Maximum Power Dissipation	T <sub>C</sub> = 125 °C	$P_{D}$	45	VV
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	-55 to +175	°C
Soldering Recommendations (Peak Temperature) d, e			260	C

THERMAL RESISTANCE RATINGS			
PARAMETER	SYMBOL	LIMIT	UNIT
Junction-to-Ambient PCB	Mount <sup>c</sup> R <sub>thJA</sub>	50	°C/W
Junction-to-Case (Drain)	R <sub>thJC</sub>	1.1	C/VV

#### Notes

- a. Package limited.
- b. Pulse test; pulse width  $\leq$  300  $\mu$ s, duty cycle  $\leq$  2 %.
- c. When mounted on 1" square PCB (FR4 material).
- d. See solder profile (<a href="www.vishay.com/doc?73257">www.vishay.com/doc?73257</a>). The PowerPAK 8x8L is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
- e. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components.

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PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static	1						
Drain-Source Breakdown Voltage	$V_{DS}$	V <sub>GS</sub>	= 0, I <sub>D</sub> = 250 μA	40	-	-	V
Gate-Source Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =	- V <sub>GS</sub> , I <sub>D</sub> = 250 μA	1.5	2	2.5	\ \
Gate-Source Leakage	I <sub>GSS</sub>	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$		-	-	± 100	nA
		V <sub>GS</sub> = 0 V	V <sub>DS</sub> = 40 V	-	-	1	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>GS</sub> = 0 V	V <sub>DS</sub> = 40 V, T <sub>J</sub> = 125 °C	-	-	50	μΑ
		V <sub>GS</sub> = 0 V	V <sub>DS</sub> = 40 V, T <sub>J</sub> = 175 °C	-	-	500	1
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	V <sub>GS</sub> = 10 V	$V_{DS} \ge 5 V$	100	-	-	Α
		V <sub>GS</sub> = 10 V	I <sub>D</sub> = 20 A	-	0.0009	0.0012	
Dynin Course On State Desistance 3	В	V <sub>GS</sub> = 4.5 V	I <sub>D</sub> = 10 A	-	0.0011	0.0015	
Drain-Source On-State Resistance a	R <sub>DS(on)</sub>	V <sub>GS</sub> = 10 V	I <sub>D</sub> = 20 A, T <sub>J</sub> = 125 °C	-	-	0.0018	Ω
		V <sub>GS</sub> = 10 V	I <sub>D</sub> = 20 A, T <sub>J</sub> = 175 °C	-	_	0.0022	
Forward Transconductance b	9 <sub>fs</sub>	V <sub>DS</sub>	= 15 V, I <sub>D</sub> = 15 A	-	122	-	S
Dynamic <sup>b</sup>							
Input Capacitance	C <sub>iss</sub>			-	10 810	14 500	
Output Capacitance	C <sub>oss</sub>	$V_{GS} = 0 V$	V <sub>DS</sub> = 25 V, f = 1 MHz	=	6500	8500	pF
Reverse Transfer Capacitance	C <sub>rss</sub>			-	700	950	
Total Gate Charge <sup>c</sup>	Qg			-	140	220	
Gate-Source Charge <sup>c</sup>	$Q_{gs}$	V <sub>GS</sub> = 10 V	$V_{DS} = 20 \text{ V}, I_D = 10 \text{ A}$	=	30	-	nC
Gate-Drain Charge <sup>c</sup>	$Q_{gd}$			-	20	-	]
Gate Resistance	$R_g$		f = 1 MHz	0.45	0.99	1.50	Ω
Turn-On Delay Time <sup>c</sup>	t <sub>d(on)</sub>			-	24	40	
Rise Time <sup>c</sup>	t <sub>r</sub>	$V_{DD} = 20 \text{ V}, \text{ R}_L = 2 \Omega$ $I_D \cong 10 \text{ A}, \text{ V}_{GEN} = 10 \text{ V}, \text{ R}_g = 1 \Omega$		-	60	100	ns
Turn-Off Delay Time <sup>c</sup>	t <sub>d(off)</sub>			-	60	100	
Fall Time <sup>c</sup>	t <sub>f</sub>			-	30	50	
Source-Drain Diode Ratings and Cha	racteristics <sup>b</sup>						
Pulsed Current <sup>a</sup>	I <sub>SM</sub>			-	-	200	Α
		I <sub>F</sub> = 50 A, V <sub>GS</sub> = 0					1

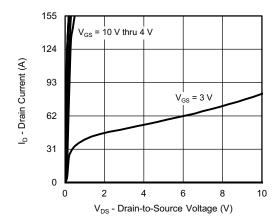
#### Notes

- a. Pulse test; pulse width  $\leq 300~\mu s,$  duty cycle  $\leq 2~\%.$
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

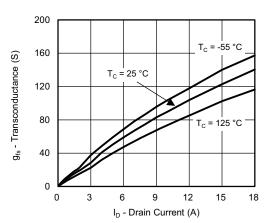
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



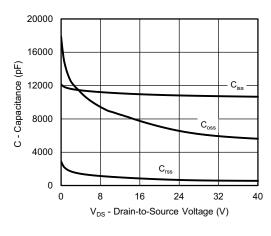
### **TYPICAL CHARACTERISTICS** (T<sub>A</sub> = 25 °C, unless otherwise noted)



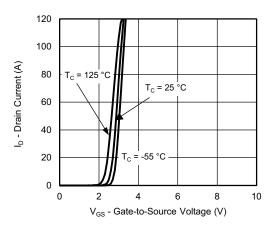
#### **Output Characteristics**



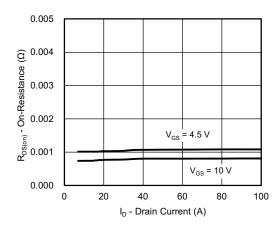
Transconductance



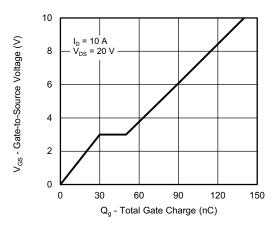
Capacitance



**Transfer Characteristics** 



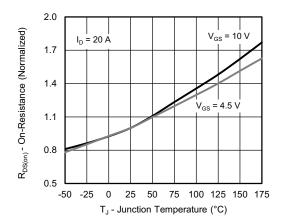
On-Resistance vs. Drain Current



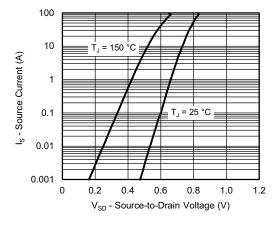
**Gate Charge** 



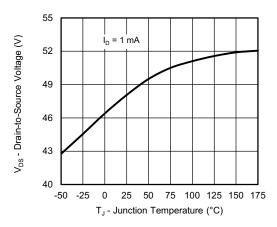
### **TYPICAL CHARACTERISTICS** (T<sub>A</sub> = 25 °C, unless otherwise noted)



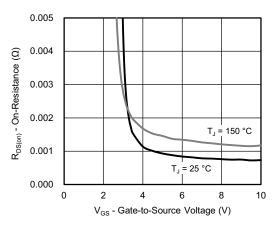
On-Resistance vs. Junction Temperature



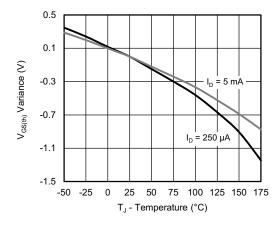
**Source Drain Diode Forward Voltage** 



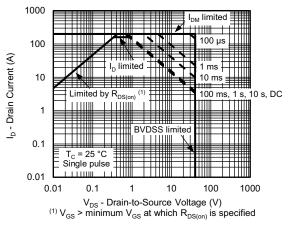
Drain Source Breakdown vs. Junction Temperature



On-Resistance vs. Gate-to-Source Voltage



**Threshold Voltage** 

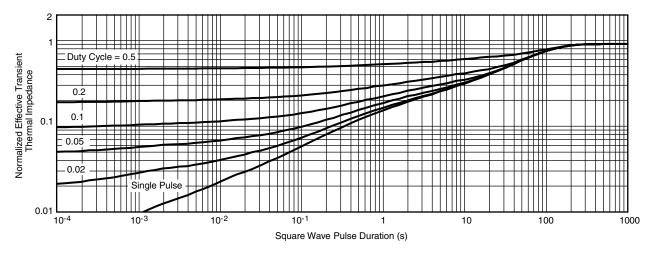


Safe Operating Area

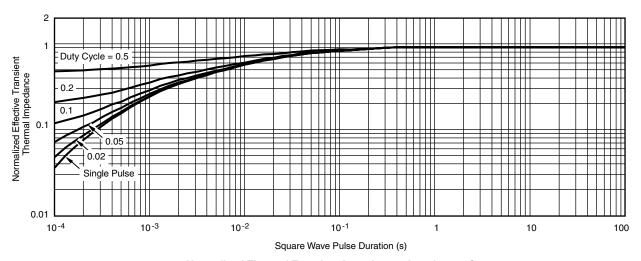
For technical questions, contact: automostech



### **THERMAL RATINGS** (T<sub>A</sub> = 25 °C, unless otherwise noted)



#### Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Case

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see <a href="https://www.vishay.com/ppg?68443">www.vishay.com/ppg?68443</a>.





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## PowerPAK® 8 x 8L

Ordering codes for the SQ rugged series power MOSFETs in the PowerPAK 8 x 8L package:

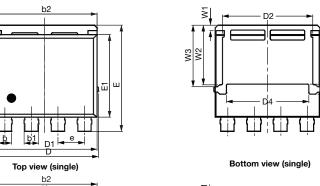
DATASHEET PART NUMBER	OLD ORDERING CODE <sup>a</sup>	NEW ORDERING CODE
SQJQ100EL	-	SQJQ100EL-T1_GE3
SQJQ402E	SQJQ402E-T1-GE3	SQJQ402E-T1_GE3
SQJQ410EL	-	SQJQ410EL-T1_GE3
SQJQ900E	-	SQJQ900E-T1_GE3

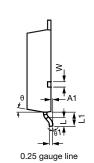
#### Note

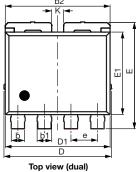
a. Old ordering code is obsolete and no longer valid for new orders

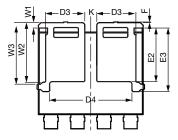


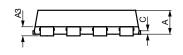
## PowerPAK® 8 x 8L Case Outline











Bottom view (dual)

DIM.	MILLIMETERS				INCHES		
DIIVI.	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.	
Α	1.70	1.80	1.90	0.067	0.071	0.075	
A1	0.00	0.08	0.13	0.000	0.003	0.005	
A3	0.55	0.62	0.70	0.022	0.024	0.028	
b	0.92	1.00	1.08	0.036	0.039	0.043	
b1	1.02	1.10	1.18	0.040	0.043	0.046	
b2	7.80	7.90	8.00	0.307	0.311	0.315	
С	0.20	0.25	0.30	0.008	0.010	0.012	
D	8.00	8.10	8.25	0.315	0.319	0.325	
D1	7.80	7.90	8.00	0.307	0.311	0.315	
D2	6.70	6.80	6.90	0.264	0.268	0.272	
D3	2.85	2.95	3.05	0.112	0.116	0.120	
D4	6.11	6.21	6.31	0.241	0.244	0.248	
е	1.95	2.00	2.05	0.077	0.079	0.081	
Е	7.90	8.00	8.10	0.311	0.315	0.319	
E1	6.12	6.22	6.32	0.241	0.245	0.249	
E2	3.94	4.04	4.14	0.140	0.159	0.163	
E3	4.69	4.79	4.89	0.185	0.189	0.193	
F	0.05	0.10	0.15	0.002	0.004	0.006	
L	0.62	0.72	0.82	0.024	0.028	0.032	
L1	0.92	1.07	1.22	0.036	0.042	0.048	
K	0.80	0.90	1.00	0.031	0.035	0.039	
W	0.30	0.40	0.50	0.012	0.016	0.020	
W1	0.30	0.40	0.50	0.012	0.016	0.020	
W2	4.39	4.49	4.59	0.173	0.177	0.181	
W3	4.54	4.64	4.74	0.179	0.183	0.187	
θ	6°	10°	14°	6°	10°	14°	
θ1	0°	3°	8°	0°	3°	8°	

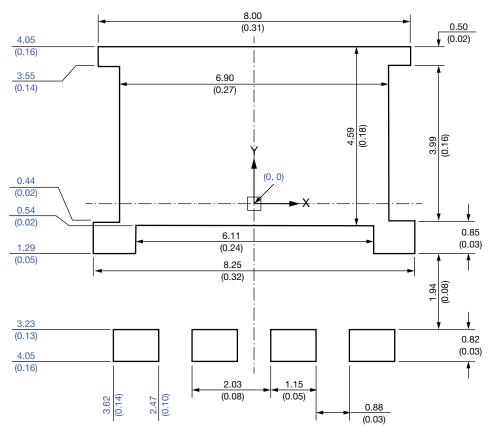
DWG: 6026

Revision: 06-Oct-14

Document Number: 67734



# Recommended Minimum PADs for PowerPAK® 8 x 8L Single



#### Dimensions in millimeters (inches)

#### Note

· Linear dimensions are in black, the same information is provided in ordinate dimensions which are in blue.



### **Legal Disclaimer Notice**

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